

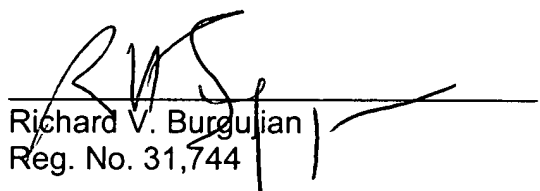
A marked up version of the amended claims is attached and captioned  
"Appendix Detailing Amendments to the Claims Pursuant to 37 C.F.R. §  
1.121(c)(ii)."

The examiner is respectfully requested to consider the above preliminary  
amendment prior to examination of the application. If there are any fees due in  
connection with the filing of this Preliminary Amendment, please charge the fees  
to Deposit Account No. 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW,  
GARRETT & DUNNER, L.L.P.

By:

  
Richard V. Burgulian  
Reg. No. 31,744

Date: August 20, 2001  
RVB/FPD/sci

LAW OFFICES

FINNEGAN, HENDERSON,  
FARABOW, GARRETT,  
& DUNNER, L.L.P.  
1300 I STREET, N. W.  
WASHINGTON, DC 20005  
202-408-4000

**APPENDIX DETAILING AMENDMENTS TO THE  
CLAIMS PURSUANT TO 37 C.F.R. § 1.121(c)(ii)**

**CLAIM AMENDMENTS**

Applicant submits the following claims marked up for the Examiner's convenience to show the changes as required by rule 37 C.F.R. 1.121(c)(ii).

1. (Amended) An ultrasonic washing method of washing a thing to be washed by supplying ultrasonic-wave-applied cleaning fluid to the thing, said ultrasonic washing method comprising applying said ultrasonic wave to said cleaning fluid in such a manner that said ultrasonic wave is turned on and off repeatedly [at specific time intervals].

7. (Amended) The washing method according to claim 6, wherein said first ultrasonic wave and said second ultrasonic wave are applied to the thing [for] to be washed [, while being alternated] at predetermined time intervals.

13. (Amended) A semiconductor device manufacturing method comprising [:] a [first] step of washing a surface at which a pattern including an island-like structure with a width of 0.2  $\mu$  m or less and an aspect ratio of 1.0 or more has been formed by applying a [first] plurality of ultrasonic waves continuously [; and

a second step of applying a second ultrasonic wave for washing].

14. (Amended) The semiconductor device manufacturing method according to claim 13, wherein said [first] plurality of ultrasonic waves differs from each other [said second ultrasonic wave] in any one of phase, wavelength, and amplitude.

15. (Amended) A semiconductor device manufacturing method comprising [:] a [first] step of washing a surface at which metal wires are exposed by applying a [first] plurality of ultrasonic waves continuously [; and a second step of applying a second ultrasonic wave for washing].

16. (Amended) The semiconductor device manufacturing method according to claim 15, wherein said [first] plurality of ultrasonic waves differs from each other [said second ultrasonic wave] in any one of phase, wavelength, and amplitude.

17. (Amended) A method of manufacturing matrix-type display devices, comprising [:] a [first] step of washing a surface at which Si or metal wires are exposed by applying a [first] plurality of ultrasonic waves continuously [; and a second step of applying a second ultrasonic wave for washing].

18. (Amended) The method according to claim 17, wherein said [first] plurality of ultrasonic waves differs from each other [said second ultrasonic wave] in any one of phase, wavelength, and amplitude.

LAW OFFICES

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& DUNNER, L.L.P.  
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202-408-4000